

Description

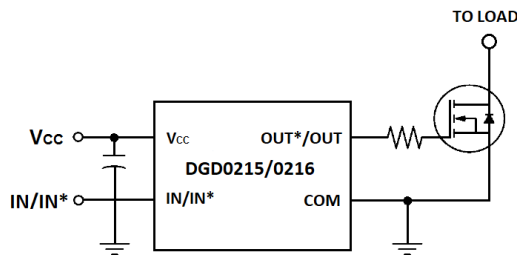
The DGD0215 and DGD0216 high speed / low side MOSFET and IGBT drivers are capable of driving 1.9A of peak current. The DGD0215 and DGD0216 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with MCUs. Fast and well matched propagation delays allow high speed operation, enabling a smaller and more compact power switching design using smaller associated components.

The DGD0215 and DGD0216 are highly resistant to noise, and are able to withstand up to 5V positive or negative on the ground pin without damage. The devices can also withstand 500mA of reverse current forced back into the outputs without damage or logic change. The DGD0215 provides an inverted output and the DGD0216 provides a non-inverting output.

The DGD0215 and DGD0216 are offered in TSOT25 package and the operating temperature extends from -40°C to +125°C.

Applications

- DC-DC Converters
- Line Drivers
- Motor Controls
- Switch Mode Power Supplies



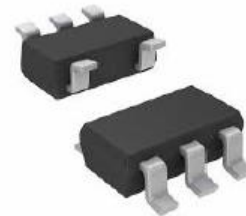
Typical Configuration

Features

- Efficient Low Cost Solution for Driving MOSFETs and IGBTs
- Wide Supply Voltage Operating Range: 4.5V to 18V
- 1.9A Source / 1.8A Sink Output Current Capability
- Inverting and Non-Inverting Input Configurations
- Fast Propagation Delay (35ns typ)
- Fast Rise and Fall Times (15ns typ)
- Logic Input (IN and IN*) 3.3V Capability
- Extended Temperature Range: -40°C to +125°C
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: TSOT25 (Type TH)
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (g3)
- Weight: 0.012 grams (Approximate)



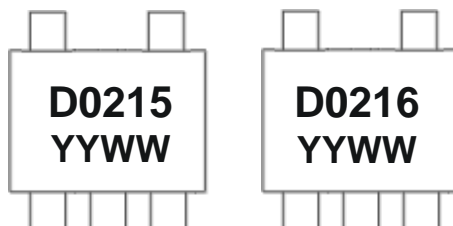
TSOT25

Ordering Information (Note 4)

Part number	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
				Qty.	Carrier
DGD0215WT-7	D0215	7	8	3,000	Reel
DGD0216WT-7	D0216	7	8	3,000	Reel

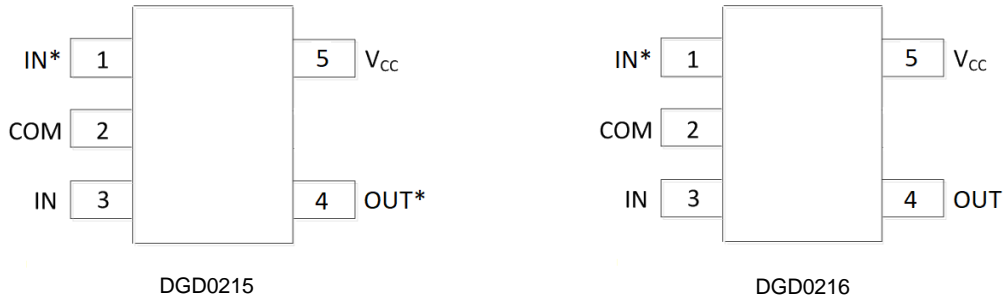
- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



D0215/D0216 = Product Type Marking Code
YY = Year (ex: 21 = 2021)
WW = Week (01 to 53)

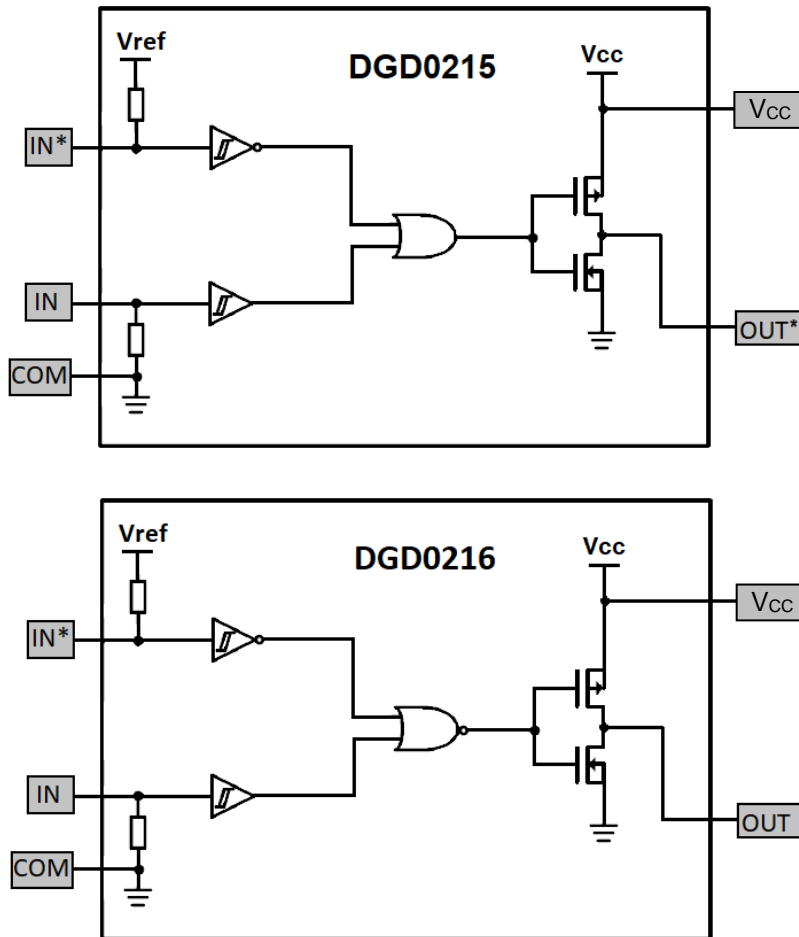
Pin Diagrams



Pin Descriptions

Pin Number	Pin Name	Function
1	IN*	Logic Input, In Phase with OUT* (DGD0215), Out of Phase with OUT (DGD0216), leave open when not in use.
2	COM	Supply Return
3	IN	Logic Input, Out of Phase with OUT* (DGD0215), In Phase with OUT (DGD0216), leave open when not in use.
4	OUT*/OUT	Gate Drive Output
5	Vcc	Supply Input

Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Low-side Fixed Supply Voltage	V _{CC}	-0.3 to +22	V
Output Voltage (OUT/OUT*)	V _{OUT}	-0.3 to V _{CC} +0.3	V
Logic Input Voltage (IN and IN*)	V _{IN}	-5 to V _{CC} +0.3	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P _D	0.54	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	188	°C/W
Operating Temperature	T _J	+150	°C
Lead Temperature (Soldering, 10s)	T _L	+300	
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2

Note: 6. Refer to JEDEC specification JESD22-A114.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _B	4.5	18	V
Output Voltage (OUT/OUT*)	V _S	0	V _{CC}	V
Logic Input Voltage (IN and IN*)	V _{IN}	0	5	V
Ambient Temperature	T _A	-40	+125	°C

DC Electrical Characteristics (V_{BIAS} (4.5V < V_{CC} < 18V), @ T_A = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Logic "1" Input Voltage	V_{IH}	2.4	1.6	—	V	—
Logic "0" Input Voltage	V_{IL}	—	1.3	0.8	V	—
Logic "1" Input Bias Current	I_{IN+}	—	—	5	μA	$V_{IN} = 3V, V_{IN^*} = 0V$
Logic "0" Input Bias Current	I_{IN-}	—	—	2	μA	$V_{IN} = 0V, V_{IN^*} = 3V$
High Level Output Voltage, $V_{BIAS} - V_O$	V_{OH}	—	25	—	mV	—
Low Level Output Voltage	V_{OL}	—	25	—	mV	—
Quiescent V_{CC} Supply Current	I_{CCQ}	—	50	100	μA	$V_{IN} = 0V$ or 3V
Output High Short Circuit Pulsed Current	I_{O+}	—	1.9	—	A	$V_{CC} = 12V$
Output Low Short Circuit Pulsed Current	I_{O-}	—	1.8	—	A	$V_{CC} = 12V$
Output Resistance, High	R_{OH}	—	3.3	—	Ω	$I_{OUT} = 10mA, V_{CC} = 12V$
Output Resistance, Low	R_{OL}	—	2.3	—	Ω	$I_{OUT} = 10mA, V_{CC} = 12V$

Note: 7. The V_{IN} and I_{IN} parameters are applicable to the logic input pins: IN and IN*. The V_O and I_O parameters are applicable to the output pins: OUT and OUT*.

AC Electrical Characteristics (V_{BIAS} (4.5V < V_{CC} < 18V), @ T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Turn-On Rise Time	t_r	—	15	25	ns	$C_L = 1000pF, V_{CC} = 12V$
Turn-Off Fall Time	t_f	—	15	25	ns	$C_L = 1000pF, V_{CC} = 12V$
Turn-On Propagation Delay	t_{ON}	—	35	50	ns	$V_{CC} = 12V$
Turn-Off Propagation Delay	t_{OFF}	—	35	55	ns	$V_{CC} = 12V$

DC Electrical Characteristics (V_{BIAS} (4.5V < V_{CC} < 18V), @ T_C = -40°C to +125°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Logic "1" Input Voltage	V_{IH}	2.4	—	—	V	—
Logic "0" Input Voltage	V_{IL}	—	—	0.8	V	—
Logic "1" Input Bias Current	I_{IN+}	—	—	10	μA	$V_{IN} = 3V$
Logic "0" Input Bias Current	I_{IN-}	—	0	5	μA	$V_{IN} = 0V$
High Level Output Voltage, $V_{BIAS} - V_O$	V_{OH}	—	25	—	mV	—
Low Level Output Voltage	V_{OL}	—	25	—	mV	—
Quiescent V_{CC} Supply Current	I_{CCQ}	—	0.1	0.2	mA	$V_{IN} = 0V$ or 3V
Output Resistance, High	R_{OH}	—	—	10	Ω	$I_{OUT} = 10mA, V_{CC} = 12V$
Output Resistance, Low	R_{OL}	—	—	7	Ω	$I_{OUT} = 10mA, V_{CC} = 12V$

Note: 7. The V_{IN} and I_{IN} parameters are applicable to the logic input pins: IN and IN*. The V_O and I_O parameters are applicable to the output pins: OUT and OUT*.

AC Electrical Characteristics (V_{BIAS} (4.5V < V_{CC} < 18V), @ T_C = -40°C to +125°C, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Turn-On Rise Time	t_r	—	30	40	ns	$C_L = 1000pF, V_{CC} = 12V$
Turn-Off Fall Time	t_f	—	30	40	ns	$C_L = 1000pF, V_{CC} = 12V$
Turn-On Propagation Delay	t_{ON}	—	45	55	ns	$V_{CC} = 12V$
Turn-Off Propagation Delay	t_{OFF}	—	50	60	ns	$V_{CC} = 12V$

Timing Waveforms

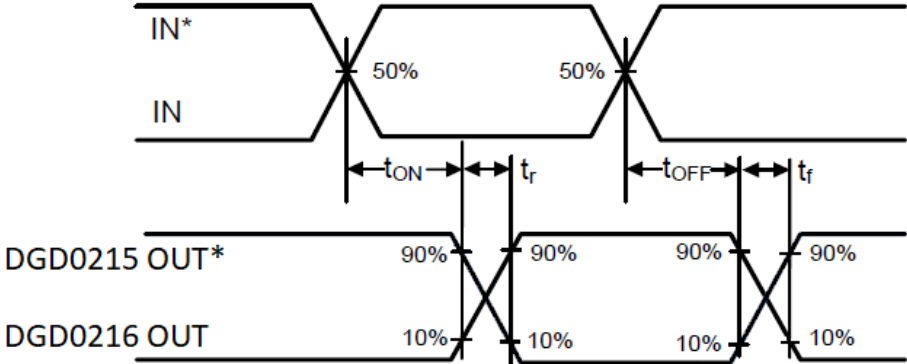


Figure 1. Switching Time Waveform Definitions

Input/Output Response Table

IN	IN*	DGD0215 (OUT*)	DGD0216 (OUT)
H	H (Open)	L	H
L	H (Open)	H	L
L (Open)	H	H	L
L (Open)	L	L	H

Typical Performance Characteristics ($V_{CC} = 12V$, $@T_A = +25^\circ C$, unless otherwise specified.)

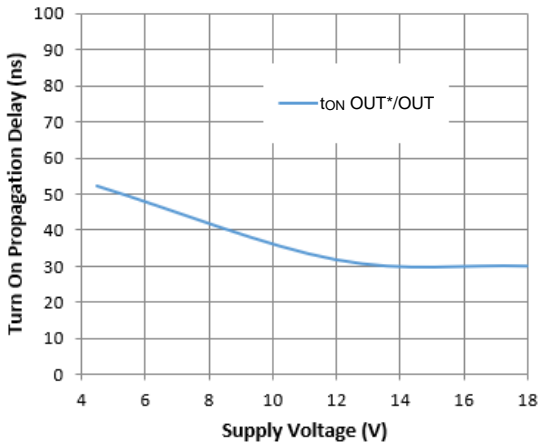


Figure 2. Turn-on Propagation Delay vs. Supply Voltage

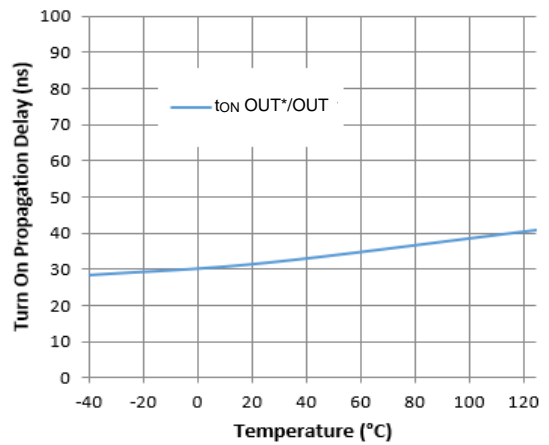


Figure 3. Turn-on Propagation Delay vs. Temperature

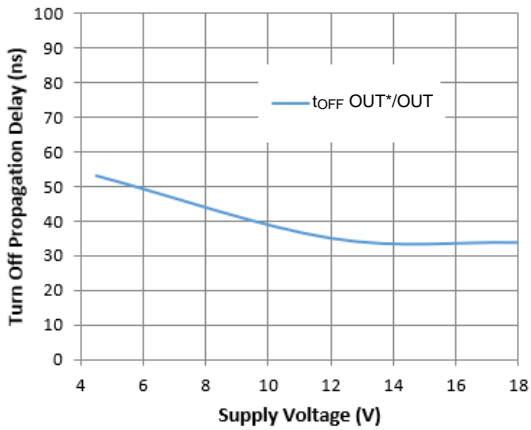


Figure 4. Turn-off Propagation Delay vs. Supply Voltage

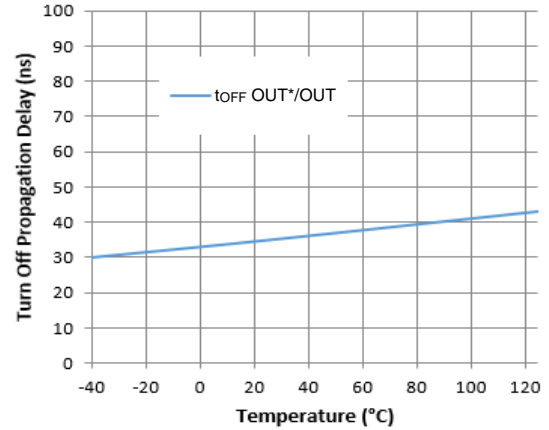


Figure 5. Turn-off Propagation Delay vs. Temperature

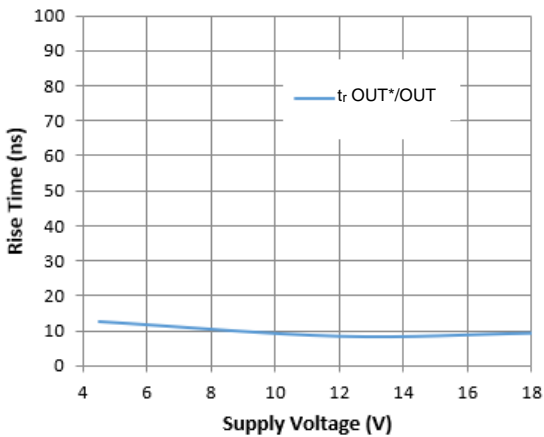


Figure 6. Rise Time vs. Supply Voltage

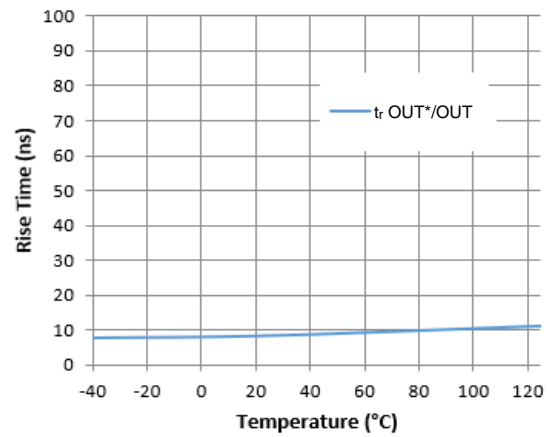


Figure 7. Rise Time vs. Temperature

Typical Performance Characteristics (continued)

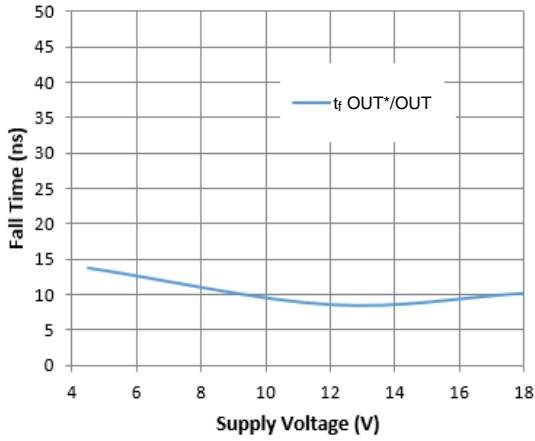


Figure 8. Fall Time vs. Supply Voltage

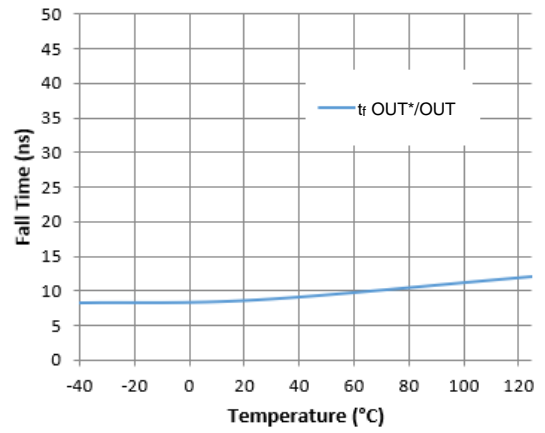


Figure 9. Fall Time vs. Temperature

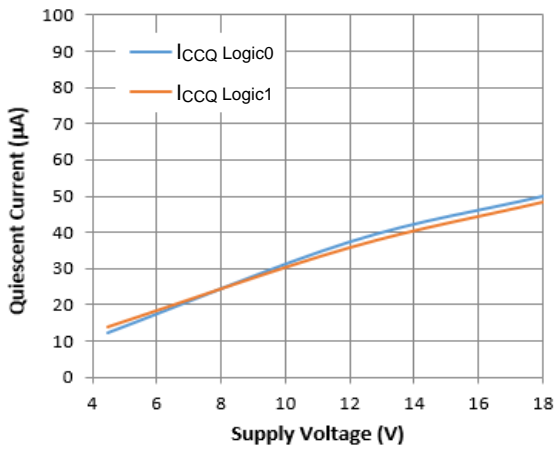


Figure 10. Quiescent Current vs. Supply Voltage

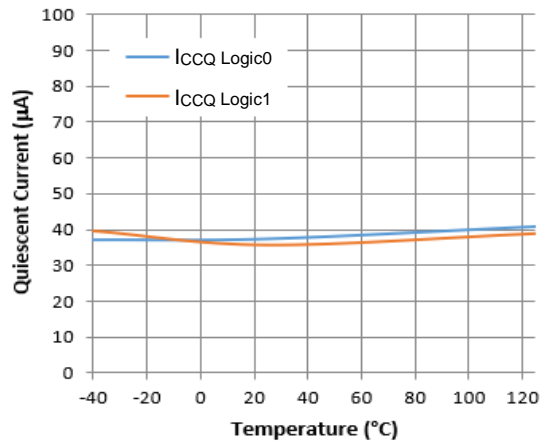


Figure 11. Quiescent Current vs. Temperature

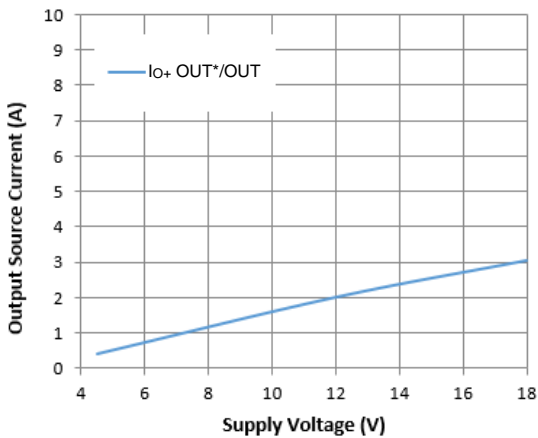


Figure 12. Output Source Current vs. Supply Voltage

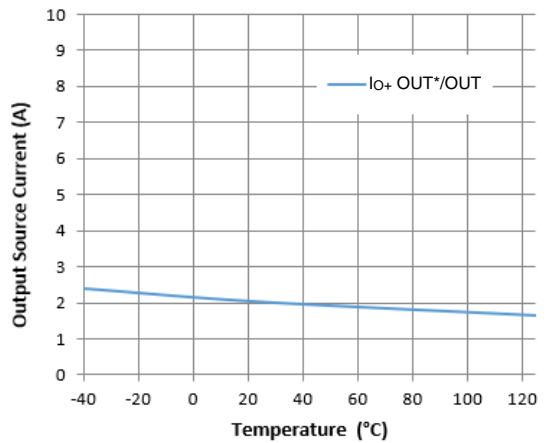


Figure 13. Output Source Current vs. Temperature

Typical Performance Characteristics (continued)

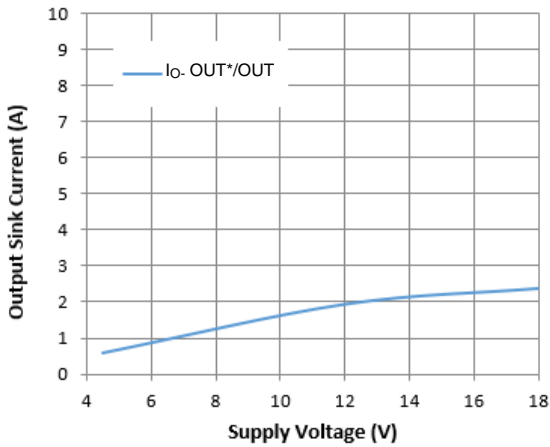


Figure 14. Output Sink Current vs. Supply Voltage

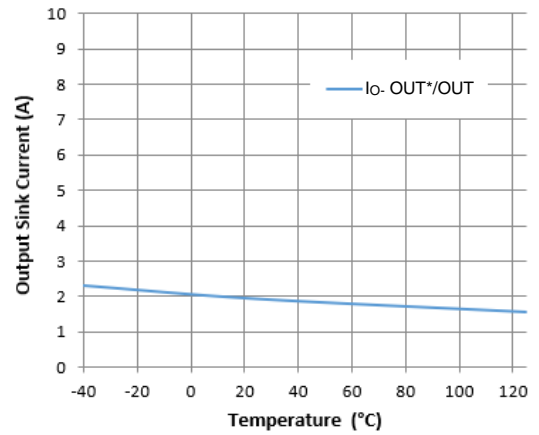


Figure 15. Output Sink Current vs. Temperature

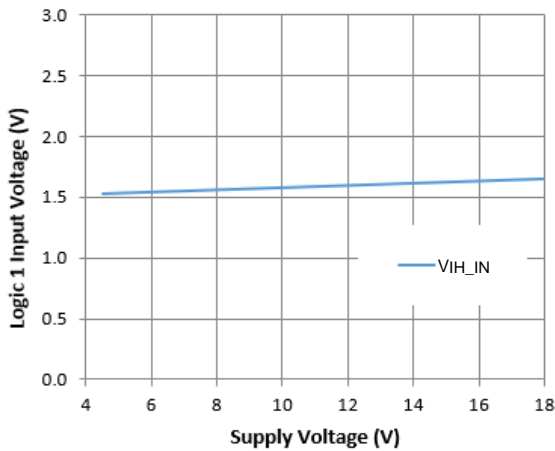


Figure 16. Logic 1 Input Voltage vs. Supply Voltage

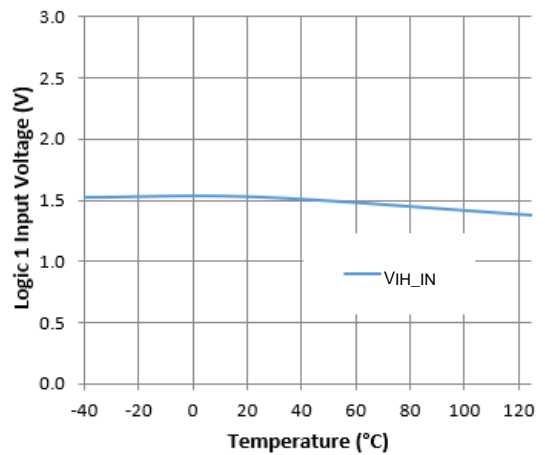


Figure 17. Logic 1 Input Voltage vs. Temperature

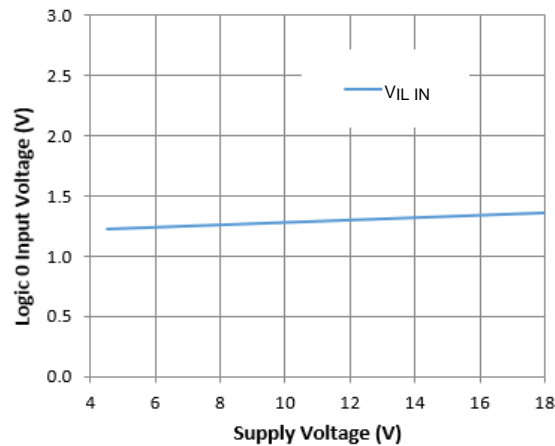


Figure 18. Logic 0 Input Voltage vs. Supply Voltage

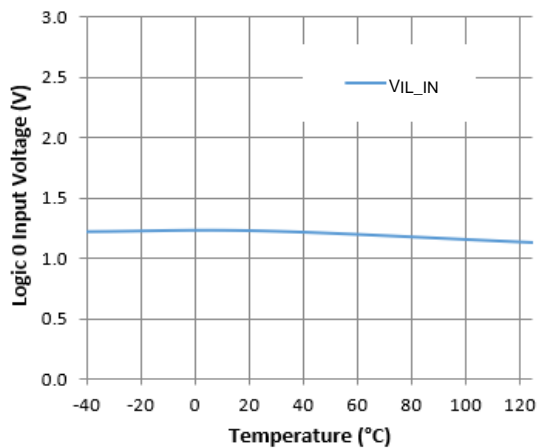


Figure 19. Logic 0 Input Voltage vs. Temperature

PCB Layout Information

The DGD0215 and DGD0216 High Speed, Low-Side, single Gate Drivers demand a fast switching current through Vcc, and in the power switching circuit a much larger current will be switched through the MOSFET. Typical applications are PFC or boost converter. Particular consideration for layout is key to ensure optimal operation of the Gate Driver IC as well as to minimize ringing and noise on the power line (VBUS) and ground. Figure 20 shows an example layout of the DGD0216 in the Low-Side power switching of a PFC circuit. Figure 21 shows the schematic of the layout shown in Figure 20, followed by a description of layout considerations for the DGD0215 and DGD0216.

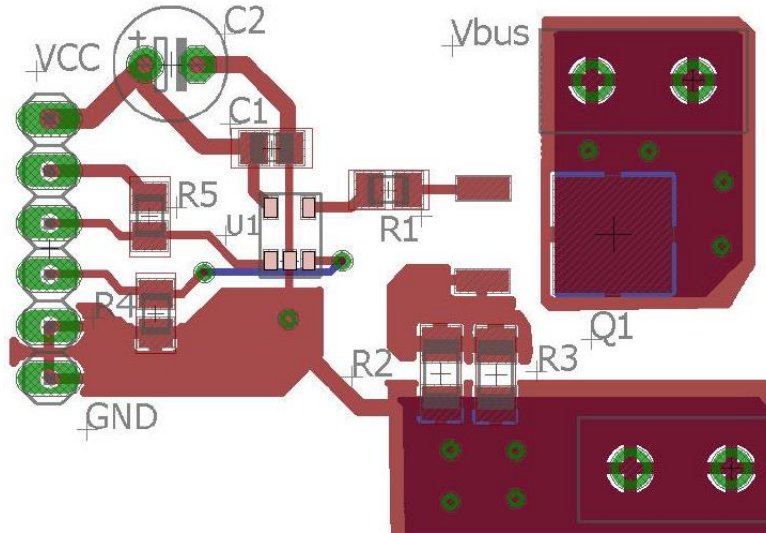


Figure 20. Example layout of DGD0216 driving a Low-Side MOSFET (for example PFC circuit)

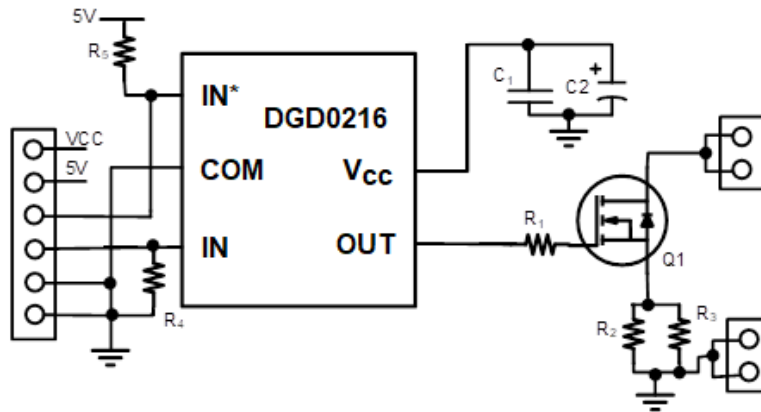


Figure 21. Schematic for layout example circuit shown in figure 20

In Gate Driver circuits, most of the current occurs during turning on/off, so when designing optimal layout, it is best to consider the charge transfer during turn on/off.

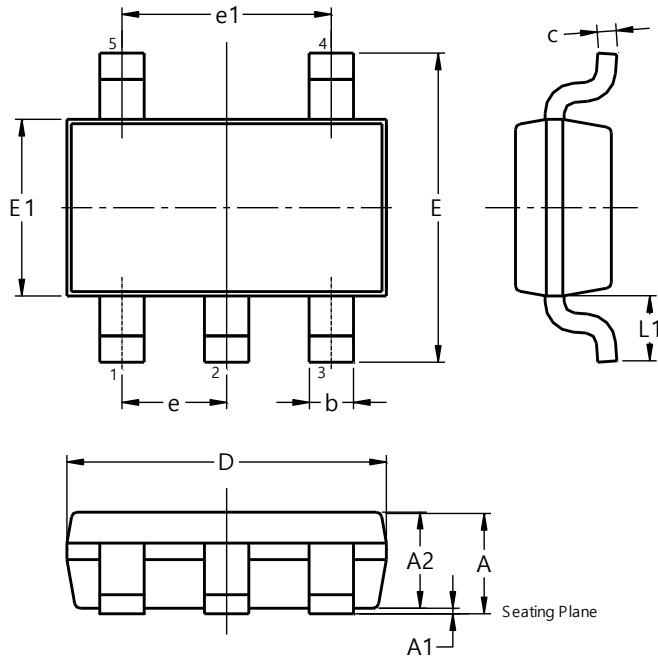
When the DGD0216 turns on, charge will flow from C₁/C₂ through the logic circuits in the Gate Driver IC and directly to GND. But the majority of the charge will flow from C₁/C₂ via the internal P-channel MOSFET (see Functional Block Diagram Output Stage), through the OUT pin to charge the Gate of the MOSFET, Q₁; the return is from the Source of Q₁ through the current sense resistors (R₂ and R₃) and to GND (back to C₁/C₂).

Hence this loop must be as short as possible to minimize stray inductance. C₁ should be a low ESR ceramic capacitor and along with gate resistor (R₁) and MOSFET (Q₁) should be located close to the DGD0216 to minimize the inductance of that loop. When the device turns off, the charge on the MOSFET Gate sinks current into the IC through the internal N-channel MOSFET to GND.

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT25 (Type TH)

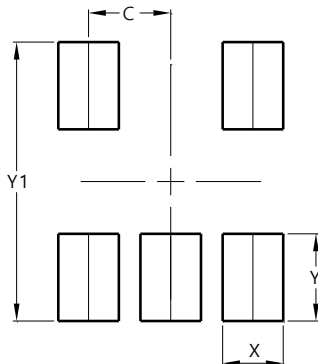


TSOT25 (Type TH)			
Dim	Min	Max	Typ
A	--	1.10	--
A1	0.01	0.10	--
A2	0.70	1.00	0.90
b	0.30	0.50	--
c	0.08	0.20	--
D	2.90 BSC		
E	2.80 BSC		
E1	1.60 BSC		
e	0.95 BSC		
e1	1.90 BSC		
L1	0.60 REF		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT25 (Type TH)



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

IMPORTANT NOTICE

1. DIODES INCORPORATED AND ITS SUBSIDIARIES (“DIODES”) MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes products. Diodes products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of the Diodes products for their intended applications, (c) ensuring their applications, which incorporate Diodes products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes’ websites, harmless against all damages and liabilities.
4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes’ website) under this document.
5. Diodes products are provided subject to Diodes’ Standard Terms and Conditions of Sale (<https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/>) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
6. Diodes products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

Copyright © 2021 Diodes Incorporated

www.diodes.com

单击下面可查看定价，库存，交付和生命周期等信息

[>>Diodes Incorporated\(达达科技\(美台\)\)](#)